

Features

1. High dv/dt
2. High surge capability
3. Standard package hermetic metal case with ceramic insulator
4. Compression Bonded Encapsulation for heavy duty operations such as severe thermal cycling
5. Types up to 1600V

Typical Applications

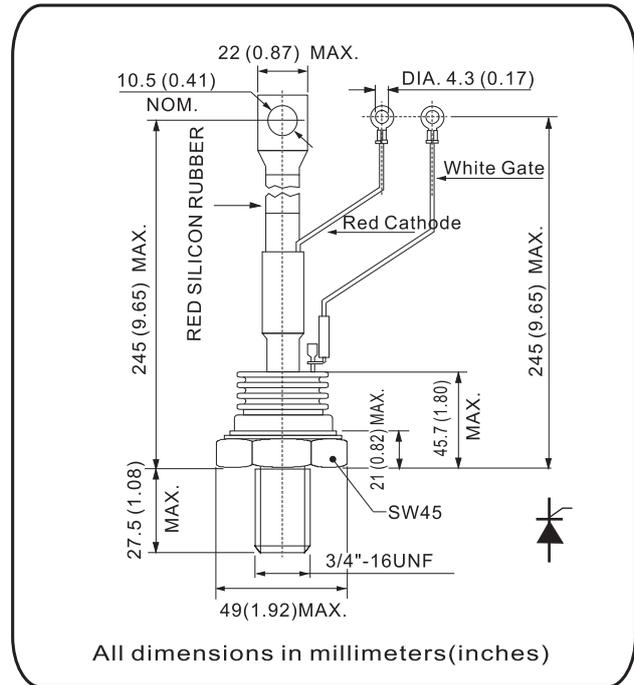
- DC motor control
- Controlled DC power supplies
- AC controllers

Ordering code

500	PT	16	S	M
(1)	(2)	(3)	(4)	(5)

- (1) Maximum average on-state current, A
 (2) For phase control thyristors
 (3) Voltage code, code x 100 = V_{RRM}/V_{DRM}
 (4) For stud type
 (5) M24x1.5

PHASE CONTRAL THYRISTORS



Electrical Characteristics

Symbol	Parameter	Condition	Value	Unit
$I_T(AV)$	Mean on-state current	180° half sine wave, 50Hz Single side cooled, $T_C = 85^\circ C$	500	A
$I_T(RMS)$	Max. RMS on-state current	Single side cooled	794	A
V_{RRM} V_{DRM}	Repetitive peak off-state voltage Repetitive peak reverse voltage	$V_{DRM} \& V_{RRM} \ t_p=10ms$ $V_{DsM} \& V_{RsM} = V_{DRM} \& V_{RRM} + 100V$	200 to 1600	V
I_{TSM}	Surge on-state current	8.3 ms half sine wave No voltage reapplied	10855	A
I_t^2	For fusing coordination		649	Ka^2s
$V_T(TO)$	Threshold voltage		0.84	V
r_t	On-state slope resistance		0.42	$m\Omega$
V_{TM}	Max. Forward voltage drop	$T_j=T_j \ max.$	1.5	V
I_H	Holding current	$V_A=12V, I_A=1A$	600	mA
d_{i}/dt	Cirtical rate of rise of turned-on current	Gate drive 20V, 20Ω, $t_r \leq 1\mu s$	1000	$A/\mu s$
t_q	Typical turn-off time	$I_{TM}=300A, T_j=T_j \ max. \ d_{i}/dt=20A/\mu s, V_R=50V$ $d_{v}/dt=20V/\mu s, \ Gate \ 0V \ 100\Omega$	100	μs
d_{v}/dt	Cirtical rate of rise of off-state voltage	$T_j=T_j \ max. \ linear \ to \ 80\% \ rated \ V_{DRM}$	500	$V/\mu s$
P_G	Max. average gate power	$T_j=T_j \ max. \ t_p \leq 5ms$	2	W
P_{GM}	Max. peak gate power square		10	W
I_{GT}	Gate trigger current	$V_A=12V, I_A=1A$	200	mA
V_{GT}	Gate trigger voltage		3	V
T_{stg}/T_j	Storage temperature		-40 to 150	$^\circ C$
$R_{th}(j-h)$	Thermal resistance(junction to case)	Single side cooled	0.08	K/W
T	Mounting force		48.5	Nm
W_t	Approximate weight		520	g